P-Channel 100-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

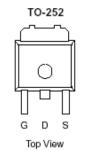
Typical	l Applica	ations:
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- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)	
-100	300 @ V _{GS} = -10V	-11 ^a	
-100	$330 @ V_{GS} = -5.5V$	-11	







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage		V_{DS}	-100	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current a	T _C =25°C	I_D	-11	Α	
Pulsed Drain Current ^b		I _{DM}	-40	ζ	
Continuous Source Current (Diode Conduction) ^a	T _C =25°C	I _S	-11	Α	
Power Dissipation ^a	T _C =25°C	P_{D}	50	W	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient °	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

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Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

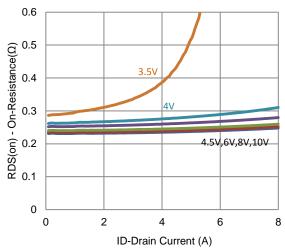
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	uA	
Zero Gate Voltage Drain Current	1	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zelo Gate Voltage Dialii Current	I _{DSS}	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-15			Α	
Drain Cauras On Basistanas a	r	$V_{GS} = -10 \text{ V}, I_{D} = -2 \text{ A}$			300	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -5.5 \text{ V}, I_D = -1.6 \text{ A}$			330	11122	
Forward Transconductance a	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -2 \text{ A}$		10		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -5.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.86		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = -50 \text{ V}, V_{GS} = -4.5 \text{ V},$		7			
Gate-Source Charge	Q_gs	$I_{D} = -2 \text{ A}$		2.3		nC	
Gate-Drain Charge	Q_gd	1D - 27		2.9			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -50 \text{ V}, R_1 = 25 \Omega,$		9			
Rise Time	t _r	$I_{DS} = -30 \text{ V}, \text{ KL} = 23 \Omega,$ $I_{D} = -2 \text{ A},$		10		nc	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		75		ns	
Fall Time	t _f	V GEN - 10 V, I GEN 0 12		52			
Input Capacitance	C _{iss}			1239			
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		121		pF	
Reverse Transfer Capacitance	C_{rss}			63			

Notes

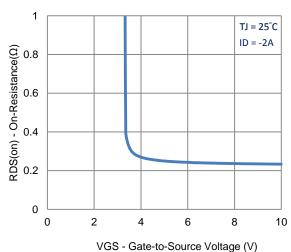
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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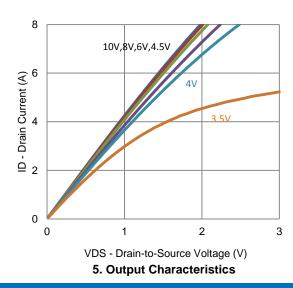
Typical Electrical Characteristics

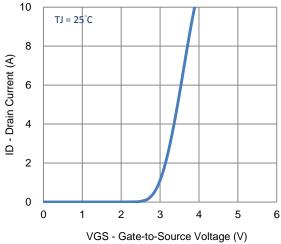


1. On-Resistance vs. Drain Current

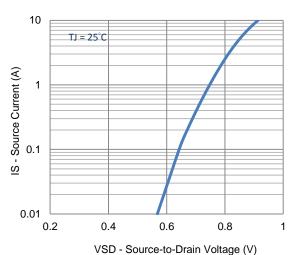


3. On-Resistance vs. Gate-to-Source Voltage

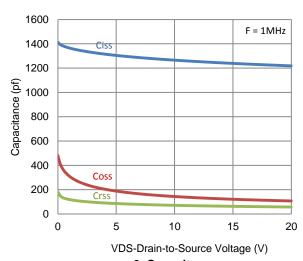




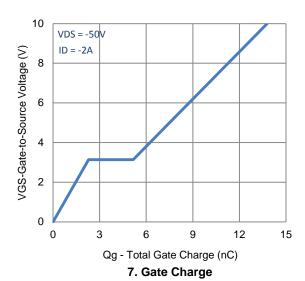
2. Transfer Characteristics



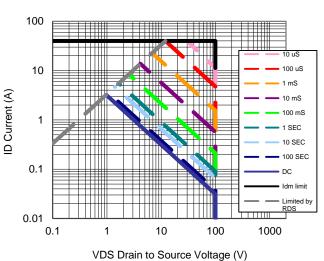
4. Drain-to-Source Forward Voltage



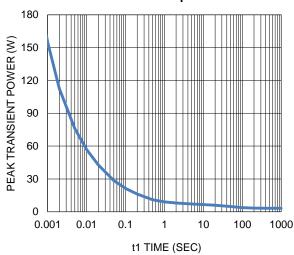
Typical Electrical Characteristics



2.5 (C) 2 (D) 3 (D) 3 (D) 4 (D) 3 (D) 4 (D) 3 (D) 4 (D)

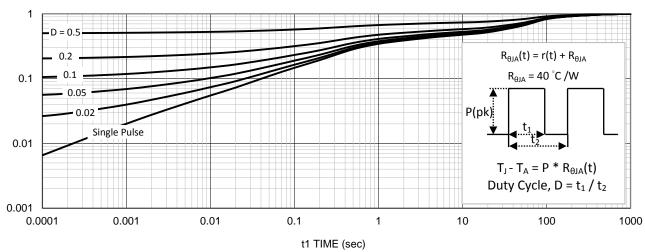






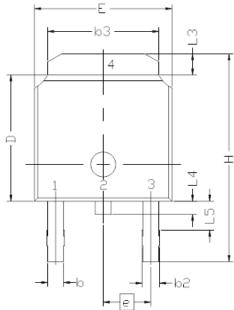
9. Safe Operating Area

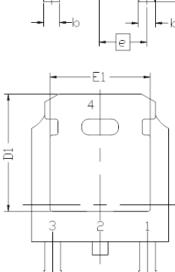
10. Single Pulse Maximum Power Dissipation



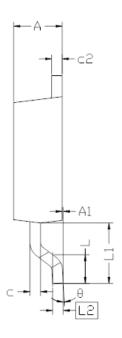
11. Normalized Thermal Transient Junction to Ambient

Package Information





SINGLE ROWNEW



SYMBOL	DIMENS: MIN	IONAL F Nom	REQMTS MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2	.743 RI	ĒF
L2	0.	.508 BS	_
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0,88
b2	0.77	0.84	1.14
b3	5,21	5.34	5.46
€		286 BS	
Α	2,20	2.30	2,38
A1	0		0.127
C	0.45	0.50	0.60
c2	0.45	0.50	0,58
D1	5,30		
E1	4.40		
θ	0°		10°

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.